Amendments to the Specification

Please replace the paragraph beginning on page 7, line 26 with the following amended paragraph:

The formation of the through holes 24 is performed by photolithography. That is, as shown in Fig. 3 by way of example, a resist film 34 is formed over the whole surface of the first conductive layer 16 and selectively exposed, followed by patterning of the resist film 34, whereby a resist pattern 34 having through holes 36 in forming predeterminate regions of the through holes 24 (see Fig. 4) is obtained. The through holes 24 are formed by etching the second insulator ~~first conductive~~ layer [[16]] 18 with the resist pattern 24 as a mask. The size of each through hole 36 defined in the resist pattern 34 is subjected to constraints by resolution of selective exposure.

Please replace the paragraph beginning on page 9, line 19 with the following amended paragraph:

Next, as shown in Fig. 7, the space formed inside each sidewall 26 is buried with a conductor material such as aluminum to thereby form a conductor [[28]] 32 which serves as a fuse. The conductor [[28]] 32 is connected to the first conductive layer 16 at its lower end.

Please replace the paragraph beginning on page 10, line 2 with the following amended paragraph:

The shape of the conductor [[28]] 32 used as a fuse is identical to that of the space 38, and its transverse cross-sectional area is smaller than that of the through hole 24. It is thus possible to obtain a fuse having a cross-sectional area smaller than the minimum dimension of the through hole 24 subjected to limitations due to the resolution of exposure and the like.